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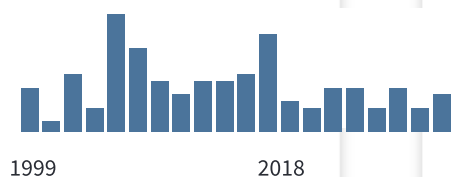
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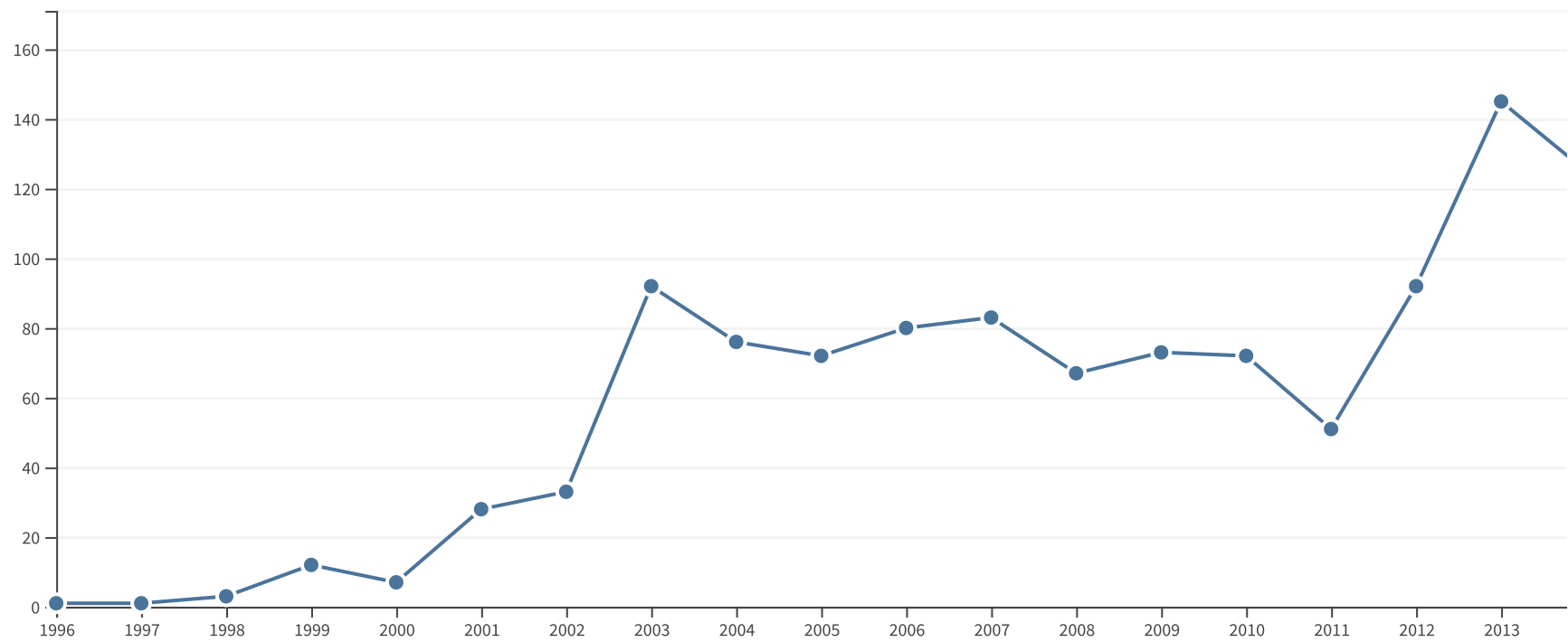
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<input type="checkbox"/>	1.	The temperature dependence of 1.3-and 1.5-μm compressively strained InGaAs(P) MQW semiconductor lasers	7	5	4	7	0	140	6.67
		By: Phillips, AF; Sweeney, SJ; Adams, AR; et al. IEEE JOURNAL OF SELECTED TOPICS IN QUANTUM ELECTRONICS Volume: 5 Issue: 3 Pages: 401-412 Published: MAY-JUN 1999							
<input type="checkbox"/>	2.	A quantitative study of radiative, Auger, and defect related recombination processes in 1.3-μm GaInNAs-based quantum-well lasers	3	2	4	1	0	125	6.94
		By: Fehse, R; Tomic, S; Adams, AR; et al. IEEE JOURNAL OF SELECTED TOPICS IN QUANTUM ELECTRONICS Volume: 8 Issue: 4 Pages: 801-810 Published: JUL-AUG 2002							
<input type="checkbox"/>	3.	Theoretical and experimental analysis of 1.3-μm InGaAsN/GaAs lasers	7	4	7	2	0	122	7.18
		By: Tomic, S; O'Reilly, EP; Fehse, R; et al. IEEE JOURNAL OF SELECTED TOPICS IN QUANTUM ELECTRONICS Volume: 9 Issue: 5 Pages: 1228-1238 Published: SEP-OCT 2003							
<input type="checkbox"/>	4.	Laser operation of Ga(NAsP) lattice-matched to (001) silicon substrate	7	22	10	6	0	94	10.44
		By: Liebich, S.; Zimprich, M.; Beyer, A.; et al. APPLIED PHYSICS LETTERS Volume: 99 Issue: 7 Article Number: 071109 Published: AUG 15 2011							
<input type="checkbox"/>	5.	Electrical injection Ga(AsBi)/(AlGa)As single quantum well laser	17	19	26	8	0	86	12.29
		By: Ludewig, P.; Knaub, N.; Hossain, N.; et al. APPLIED PHYSICS LETTERS Volume: 102 Issue: 24 Article Number: 242115 Published: JUN 17 2013							
<input type="checkbox"/>	6.	Band engineering in dilute nitride and bismide semiconductor lasers	15	13	18	12	0	85	10.63

By: Broderick, C. A.; Usman, M.; Sweeney, S. J.; et al.
SEMICONDUCTOR SCIENCE AND TECHNOLOGY Volume: 27 Issue: 9 Special Issue:
SI Article Number: 094011 Published: SEP 2012

<input type="checkbox"/>	7.	The effect of temperature dependent processes on the performance of 1.5-μm compressively strained InGaAs(P) MQW semiconductor diode lasers	6	1	5	2	0	82	3.73
		By: Sweeney, SJ; Phillips, AF; Adams, AR; et al. IEEE PHOTONICS TECHNOLOGY LETTERS Volume: 10 Issue: 8 Pages: 1076-1078 Published: AUG 1998							
<input type="checkbox"/>	8.	Carrier transport and recombination in p-doped and intrinsic 1.3 μm InAs/GaAs quantum-dot lasers	3	0	1	6	0	70	4.67
		By: Marko, IP; Masse, NF; Sweeney, SJ; et al. APPLIED PHYSICS LETTERS Volume: 87 Issue: 21 Article Number: 211114 Published: NOV 21 2005							
<input type="checkbox"/>	9.	Experimental analysis of temperature dependence in 1.3-μm AlGaInAs-InP strained MQW lasers	2	1	2	3	0	42	2.00
		By: Higashi, T; Sweeney, SJ; Phillips, AF; et al. IEEE JOURNAL OF SELECTED TOPICS IN QUANTUM ELECTRONICS Volume: 5 Issue: 3 Pages: 413-419 Published: MAY-JUN 1999							
<input type="checkbox"/>	10.	Dependence of threshold current on QW position and on pressure in 1.5 μm InGaAs(P) lasers	4	2	3	3	0	37	1.76
		By: Sweeney, SJ; Adams, AR; Silver, M; et al. Conference: 8th International Conference on High Pressure Semiconductor Physics (HPSP-VIII) Location: THESSALONIKI, GREECE Date: AUG 09-13, 1998 PHYSICA STATUS SOLIDI B-BASIC RESEARCH Volume: 211 Issue: 1 Pages: 525-531 Published: JAN 1999							

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